



THE DATASHEET OF FZT688BTA



FZT688B

SOT223 NPN SILICON PLANAR POWER HIGH GAIN TRANSISTOR ISSUE 3 - OCTOBER 1995

FEATURES

- * Extremely low equivalent on resistance
- * Gain of 400 at $I_C=3$ Amps and very low $V_{CE(sat)}$

APPLICATIONS

- * Flash gun convertors & Battery powered

PART MARKING DETAIL – FZT688B
COMPLEMENTARY TYPE - FZT788B

ABSOLUTE MAXIMUM RATINGS

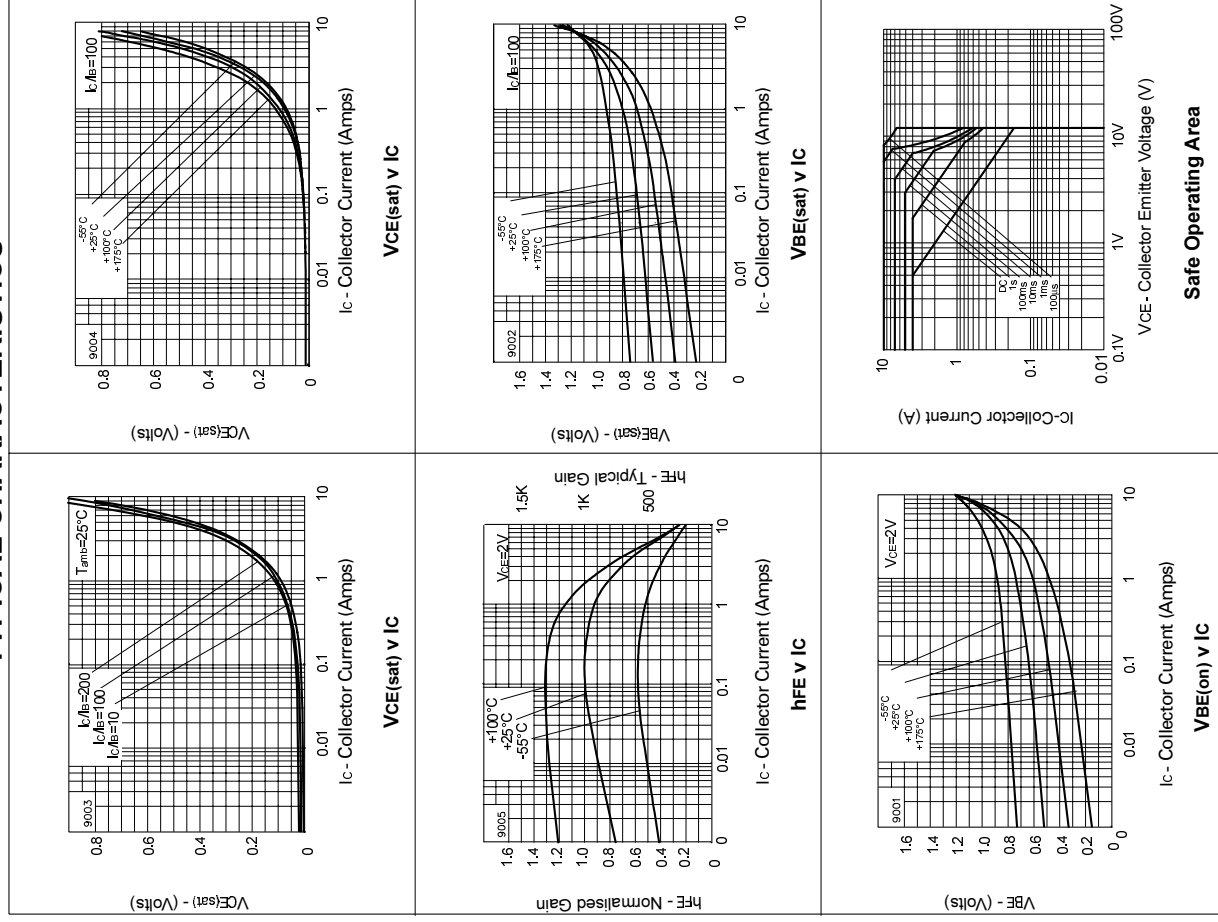
PARAMETER	SYMBOL
Collector-Base Voltage	V_{CB}
Collector-Emitter Voltage	V_{CE}
Emitter-Base Voltage	V_{EB}
Peak Pulse Current	I_{CP}
Continuous Collector Current	I_C
Power Dissipation at $T_{amb}=25^{\circ}C$	P_D
Operating and Storage Temperature	T_{STG}

ELECTRICAL CHARACTERISTICS

PARAMETER	SYMBOL
Breakdown Voltages	$V_{(BR)}$
Collector Cut-Off Current	I_{CCE}
Emitter Cut-Off Current	I_{EBE}
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$
Base-Emitter Saturation Voltage	$V_{BE(sat)}$
Base-Emitter Turn-On Voltage	$V_{BE(on)}$
Static Forward Current Transfer Ratio	h_{FE}
Transition Frequency	f_T
Input Capacitance	C_{in}
Output Capacitance	C_{out}
Switching Times	t_{on} t_{off}

*Measured under pulsed conditions. Pulsed Spice parameter data is available upon request.

TYPICAL CHARACTERISTICS



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